

**isc Silicon NPN Power Transistor**
**BUW133H**
**DESCRIPTION**

High Switching Speed

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 430V$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

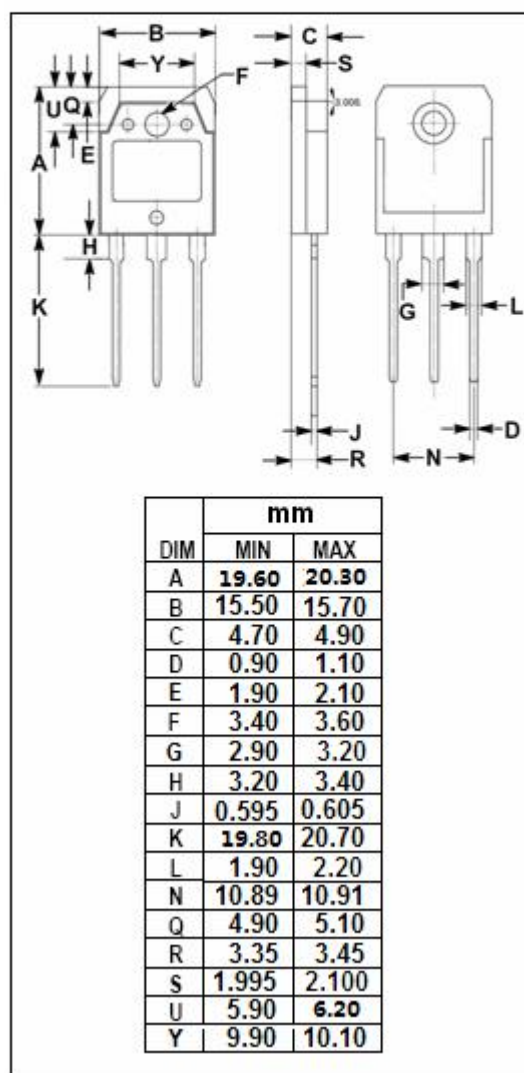
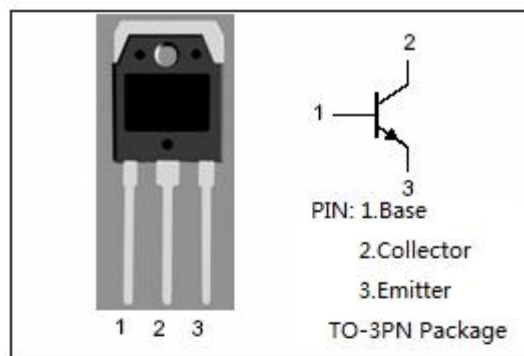
- Designed for use in very fast switching applications in inductive circuits.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	MAX	UNIT
$V_{CES}$	Collector- Emitter Voltage ( $V_{BE} = 0$ )	850	V
$V_{CEO}$	Collector-Emitter Voltage	430	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	15	A
$I_{CM}$	Collector Current-Peak	20	A
$I_B$	Base Current	10	A
$I_{BM}$	Base Current-Peak	15	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ C$	135	W
$T_j$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ C$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.93	$^\circ C/W$



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**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	430			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			2.5	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 1A			3.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 1A			1.5	V
I <sub>CBO</sub>	Collector-Base Cutoff Current	V <sub>CB</sub> =V <sub>CB0</sub> ; I <sub>E</sub> = 0 V <sub>CB</sub> =V <sub>CB0</sub> ; I <sub>E</sub> = 0; T <sub>J</sub> =100°C			0.25 1.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 15A ; V <sub>CE</sub> = 5V	7			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1kHz			400	pF

Switching Times , Resistive Load

t <sub>on</sub>	Turn-On Time	I <sub>C</sub> = 10A ; I <sub>B1</sub> = 1A; I <sub>B2</sub> = -2A		0.4		μs
t <sub>stg</sub>	Storage Time			1.3		μs
t <sub>f</sub>	Fall Time			0.15		μs

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